

**isc Silicon PNP Darlington Power Transistor**

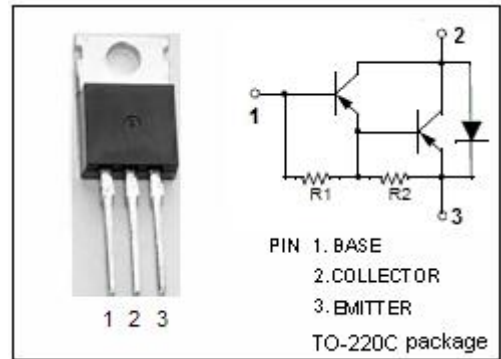
**BDX34B**

**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = -80V(\text{Min})$
- High DC Current Gain  
:  $h_{FE} = 750(\text{Min}) @ I_C = -3A$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -2.5V(\text{Max.}) @ I_C = -3A$
- Complement to Type BDX33B

**APPLICATIONS**

- Designed for general purpose amplifier and low speed switching applications.

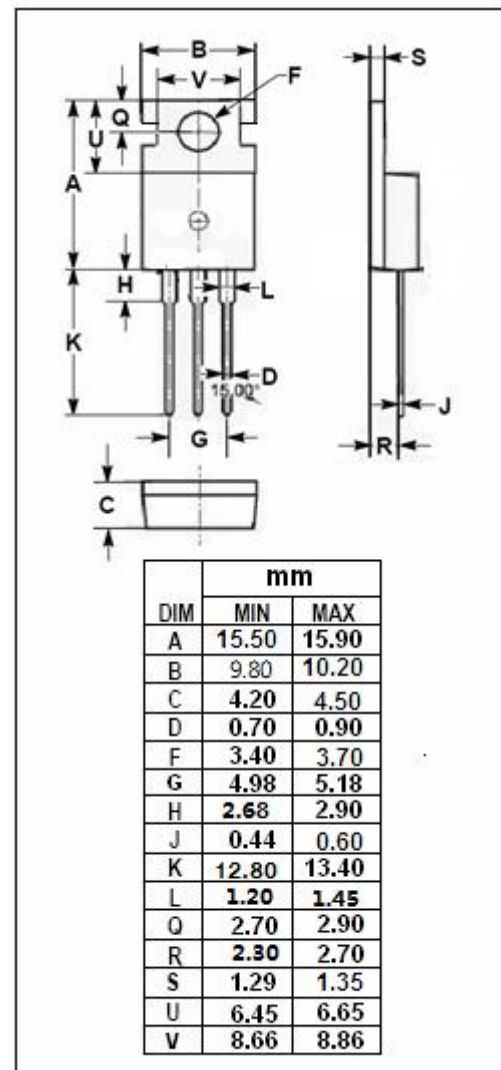


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-80	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-10	A
$I_{CM}$	Collector Current-Peak	-15	A
$I_B$	Base Current-Continuous	-0.25	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	70	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.78	$^\circ\text{C/W}$



**isc Silicon PNP Darlington Power Transistor****BDX34B****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -50\text{mA}; I_B = 0$	-80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -6\text{mA}$			-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -3\text{V}$			-2.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-0.2	mA
$I_{CEO}$	Collector Cutoff Current	$V_{CE} = -40\text{V}; I_B = 0$			-0.5	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-10	mA
$h_{FE}$	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -3\text{V}$	750			